



IRL3803VPBF Information

Part Number IRL3803VPBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 140A TO-220AB

TO-220-3 **Package**

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com

E-mail: salesdept@heisener.com





Certified Quality

For Reference Only

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IRL3803VPBF Specifications

Manufacturer Part Number IRL3803VPBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 140A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 76nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 3720pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 5.5 mOhm @ 71A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3		
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SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C140A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250µAGate Charge (Qg) (Max) @ Vgs76nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3720pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs5.5 mOhm @ 71A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C140A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs76nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3720pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs5.5 mOhm @ 71A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C140A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs76nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3720pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs5.5 mOhm @ 71A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	HEXFET?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C140A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs76nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3720pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs5.5 mOhm @ 71A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.5 mOhm @ 71A, 10V Operating Temperature Supplier Device Package Package / Case 140A (Tc) 1	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 76nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±16V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.5 mOhm @ 71A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 1V @ 250μA 76nC @ 4.5V 1720 — 4.5V 2720 — 4.5V 2	Current - Continuous Drain (Id) @ 25°C	140A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ETF Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Joperating Type Through Hole Supplier Device Package Package / Case 76nC @ 4.5V 76nC @ 4.5V 76nC @ 4.5V 3720pF @ 25V 20W CTC FET Feature	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±16V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.5 mOhm @ 71A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	1V @ 250μA
Vgs (Max)±16VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs5.5 mOhm @ 71A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	76nC @ 4.5V
FET Feature - 200W (Tc) Rds On (Max) @ Id, Vgs 5.5 mOhm @ 71A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	3720pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.5 mOhm @ 71A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±16V
Rds On (Max) @ Id, Vgs5.5 mOhm @ 71A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	200W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	5.5 mOhm @ 71A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

IRL3803VPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRL3803VPBF Payment Methods



















IRL3803VPBF Shipping Methods













If you have any question about IRL3803VPBF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com